## **SEMICONDUCTOR**

**6.0A FAST RECOVERY RECTIFIER** 

# Data Sheet 2710, Rev.—

#### **Features**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

# $\begin{array}{c|c} A & \longrightarrow & B & \longrightarrow & A & \longrightarrow \\ & \downarrow & & \downarrow & & \\ & \downarrow & & \downarrow & \\ & \uparrow & & C & \\ & D & & \end{array}$

#### **Mechanical Data**

Case: Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: Cathode BandWeight: 2.1 grams (approx.)Mounting Position: Any

Mounting Position: AnyMarking: Type Number

Epoxy: UL 94V-O rate flame retardant

R-6								
Dim	Min	Max	Min	Max				
Α	25.4	_	1.000	_				
В	8.60	9.10	0.338	0.358				
С	1.20	1.30	0.047	0.051				
D	8.60	9.10	0.338	0.358				
	In mm		In inch					

## Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	FR601	FR602	FR603	FR604	FR605	FR606	FR607	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T <sub>A</sub> = 55°C	lo	6.0							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	200							А
Forward Voltage @I <sub>F</sub> = 6.0A	VFM	FM 1.2					V		
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	lгм	10 200							μΑ
Reverse Recovery Time (Note 2)	trr	150 250 500				00	nS		
Typical Junction Capacitance (Note 3)	Cj	100							pF
Operating Temperature Range	Tj	-65 to +125						°C	
Storage Temperature Range	Тѕтс	-65 to +150						°C	

### \*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

- 2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.
- 3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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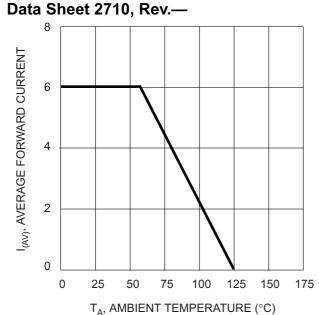
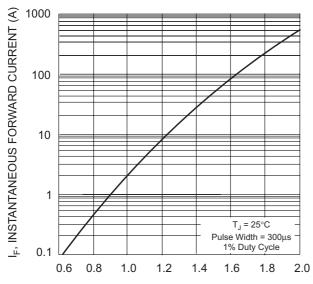
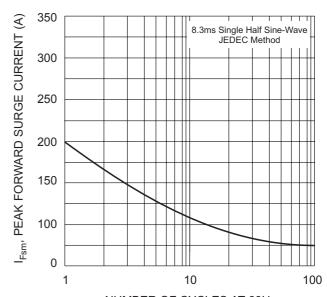


Fig. 1, Typical Forward Current Derating Curve



V<sub>F</sub>, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 3, Typical Instantaneous Forward Characteristics



NUMBER OF CYCLES AT 60Hz Fig. 2 Max Non-Repetitive Peak Surge Current

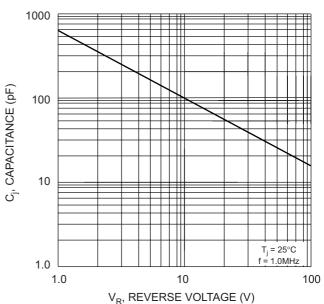
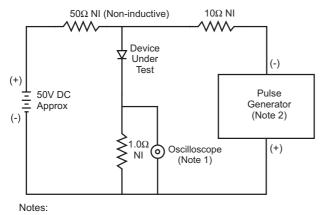
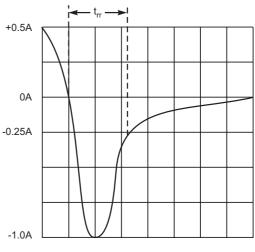


Fig. 4 Typical Junction Capacitance



- 1. Rise Time = 7.0ns max. Input Impedance = 1.0M $\Omega$ , 22pF.
- 2. Rise Time = 10ns max. Input Impedance =  $50\Omega$ .



Set time base for 5/10ns/cm

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

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